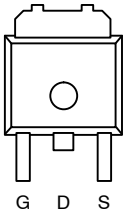
N-Channel 20-V (D-S)175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]
20	0.0045 @ V_{GS} = 4.5 V	100
	0.006 @ V_{GS} = 2.5 V	90

FEATURES

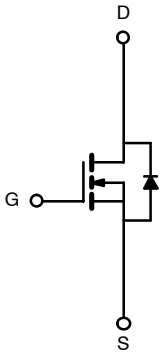
- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested

TO-252



Top View

Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±15	
Continuous Drain Current[a]	T_C = 25°C	I_D	100	A
	T_C = 100°C		80	
Pulsed Drain Current		I_{DM}	200	
Continuous Source Current (Diode Conduction)[a]		I_S	65	
Maximum Power Dissipation	T_C = 25°C	P_D	71	W
	T_A = 25°C		8.3[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b]	t ≤ 10 sec.	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	1.75	2.1	

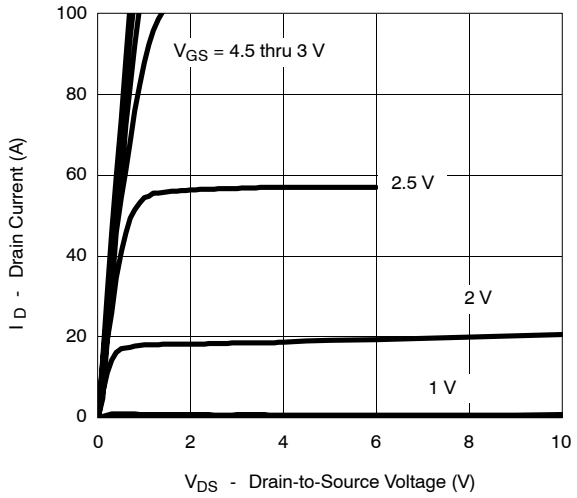
Notes
a. Package Limited
b. Surface Mounted on 1" x 1" FR4 Board
c. t ≤ 10 sec

SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Condition**	**Min**	**Typ[a]**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	0.5		1.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	μA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 125°C			50	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	100			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 20 A		0.0045		Ω
		V_{GS} = 4.5 V, I_D = 20 A, T_J = 125°C		0.0055		
		V_{GS} = 2.5 V, I_D = 20 A		0.006		
Forward Transconductance[b]	g_{fs}	V_{DS} = 5 V, I_D = 40 A	20			S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		3660		pF
Output Capacitance	C_{oss}			730		
Reverse Transfer Capacitance	C_{rss}			375		
Total Gate Charge[c]	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 40 A		26	35	nC
Gate-Source Charge[c]	Q_{gs}			5		
Gate-Drain Charge[c]	Q_{gd}			7		
Gate Resistance	R_g		1		3.7	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 10 V, R_L = 0.25 Ω I_D ≅ 40 A, V_{GEN} = 4.5 V, R_G = 2.5 Ω		20	35	ns
Rise Time[c]	t_r			120	190	
Turn-Off Delay Time[c]	$t_{d(off)}$			45	70	
Fall Time[c]	t_f			20	35	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				100	A
Diode Forward Voltage[b]	V_{SD}	I_F = 100 A, V_{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 40 A, di/dt = 100 A/μs		35	70	ns

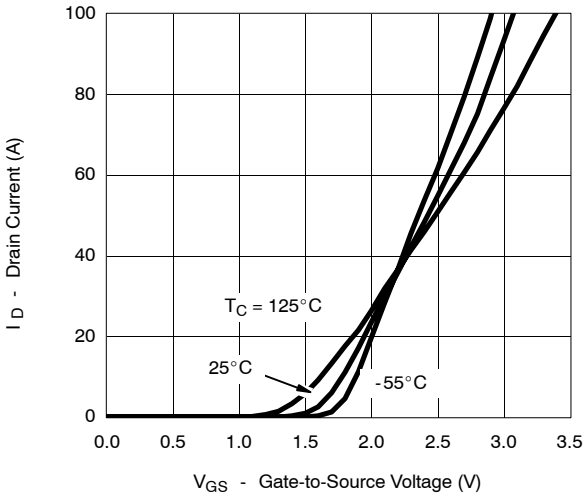
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

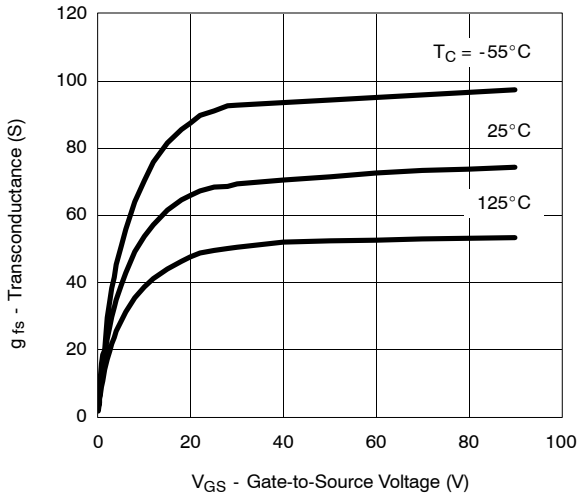
Output Characteristics



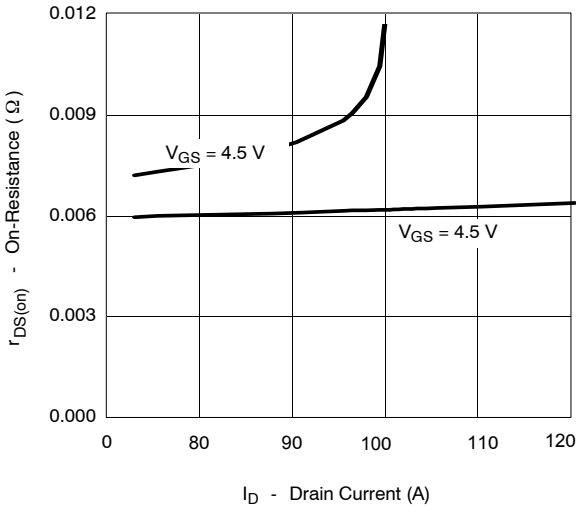
Transfer Characteristics



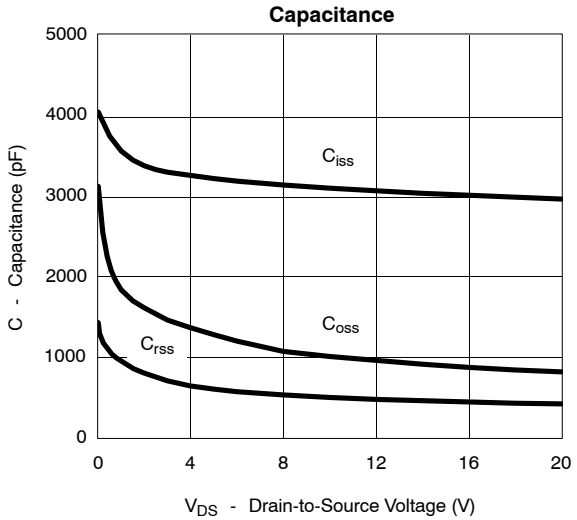
Transconductance



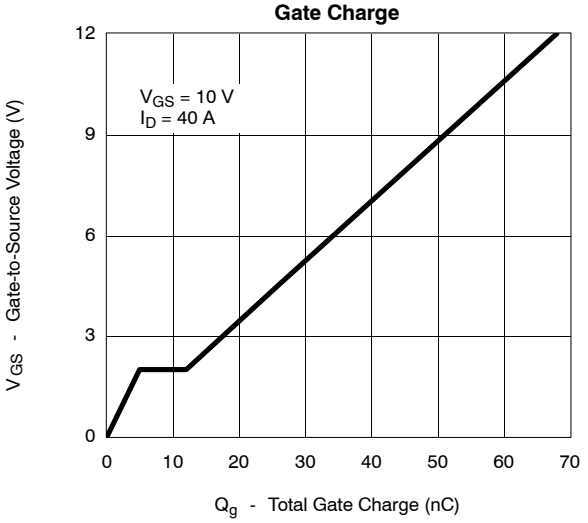
On-Resistance vs. Drain Current



Capacitance

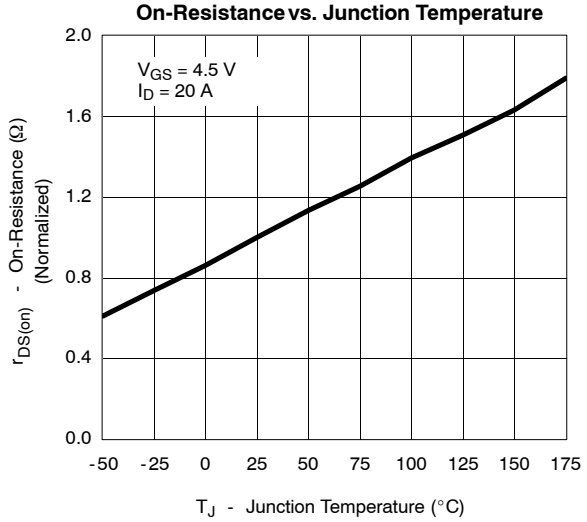


Gate Charge

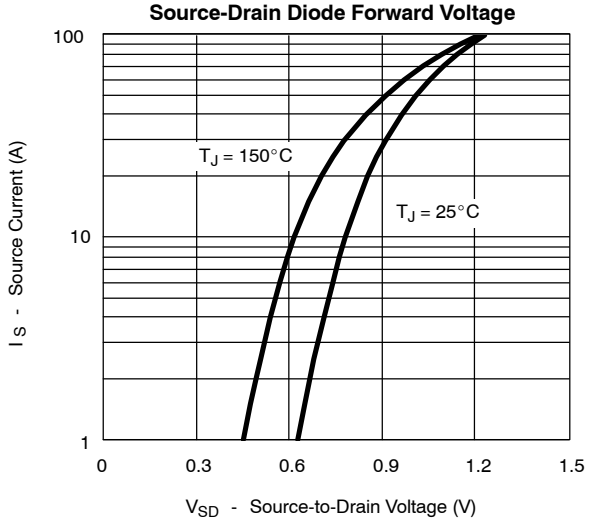


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

On-Resistance vs. Junction Temperature

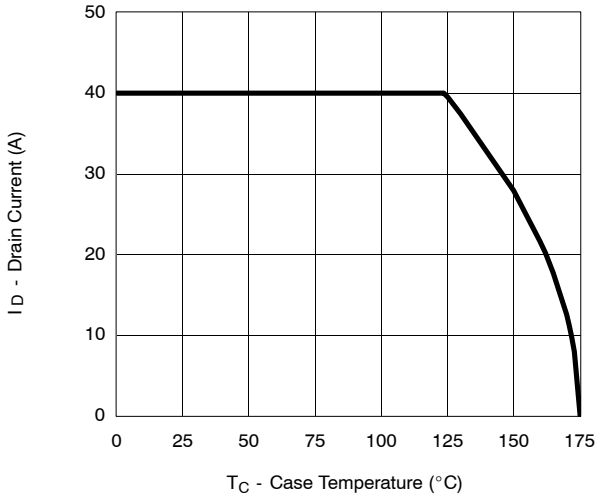


Source-Drain Diode Forward Voltage

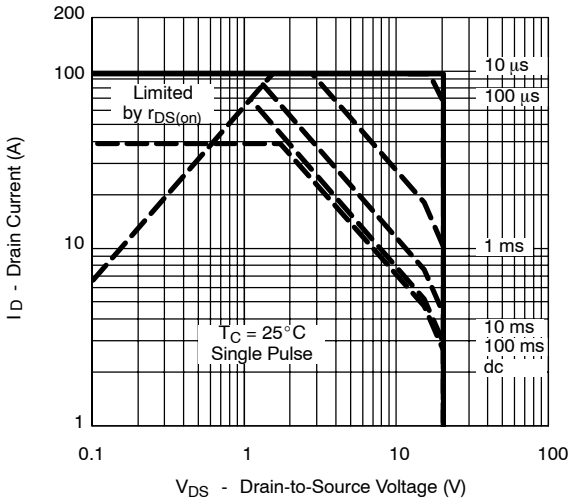


THERMAL RATINGS

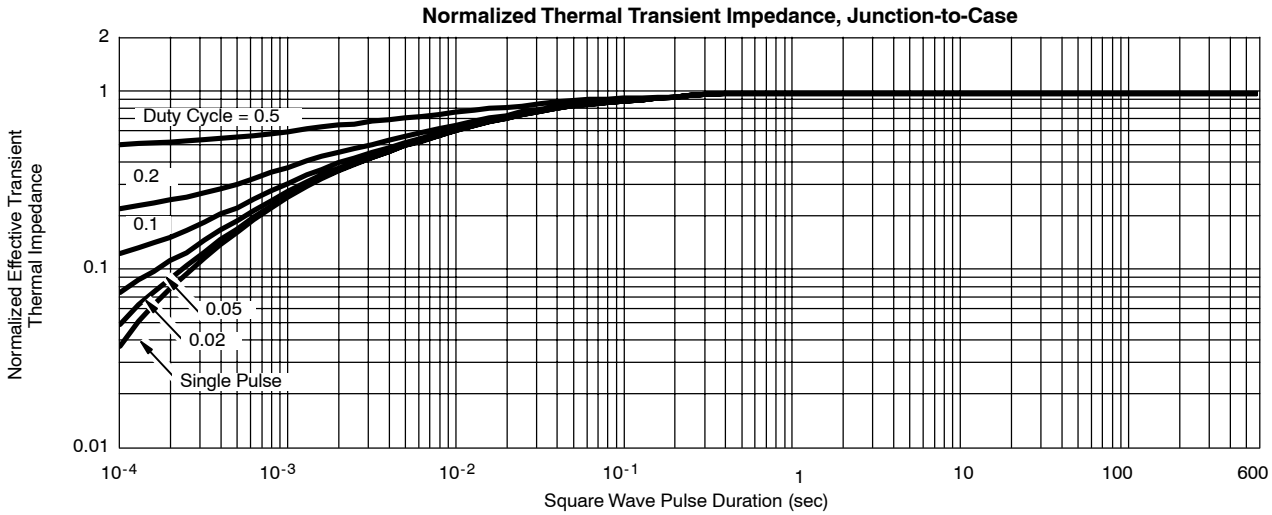
Maximum Avalanche Drain Current vs. Case Temperature



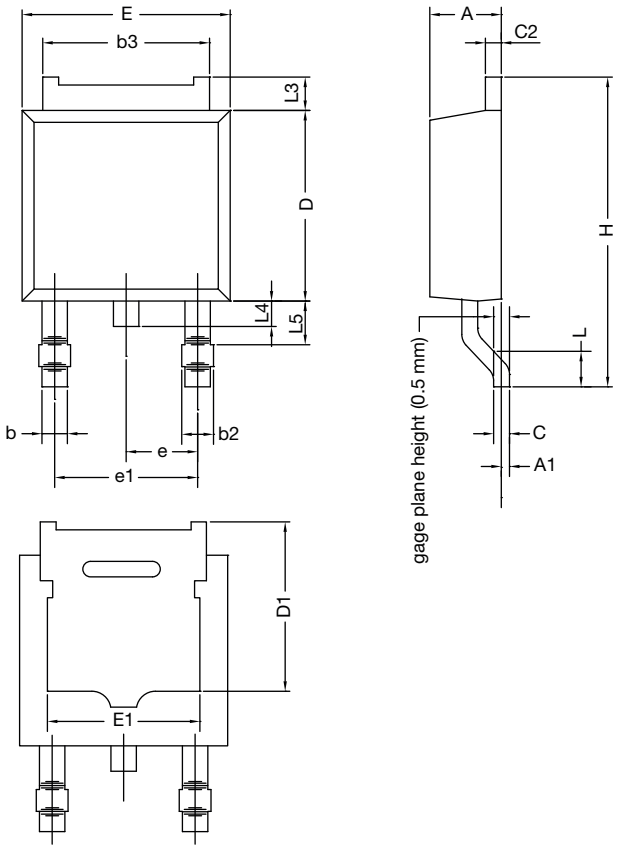
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE



	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

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